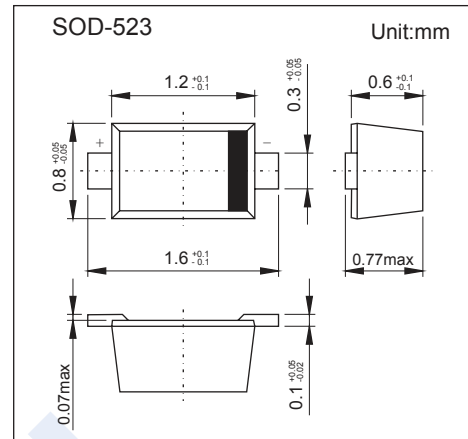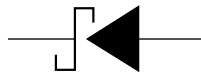## Schottky Diodes

1PS79SB70

■ Features

● Low forward voltage

● High breakdown voltage

● Guard ring protected

● Ultra small plastic SMD package

● Low capacitance.

SOD-523   Unit:mm

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	70	V
Forward Current	I_F	70	mA
Repetitive Peak Forward Current @ tp ≤ 1s; δ ≤ 0.5	I_{FRM}	70	
Non-Repetitive Peak Forward Current @ tp < 10 ms	I_{FSM}	100	
Thermal Resistance Junction to Ambient	$R_{θJA}$	450	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-65 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	I_R= 100 uA	70			V
Forward voltage	V_{F1}	I_F= 1 mA			0.41	
	V_{F2}	I_F= 10mA			0.75	
	V_{F3}	I_F= 15 mA			1	
Reverse voltage leakage current (Note.1)	I_{R1}	V_R=50 V			100	nA
	I_{R2}	V_R=70 V			10	uA

Note.1 Pulsed test: t_p= 300μs;δ= 0.02.

■ Marking

Marking	G

Schottky Diodes
1PS79SB70

■ Typical Characterisitics
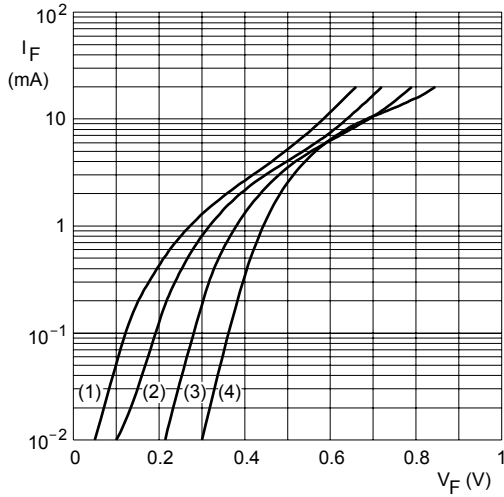
(1) T_{amb} = 125 °C. (3) T_{amb} = 25 °C.
(2) T_{amb} = 85 °C. (4) T_{amb} = −40 °C.

Fig.1 Forward current as a function of forward voltage; typical values.
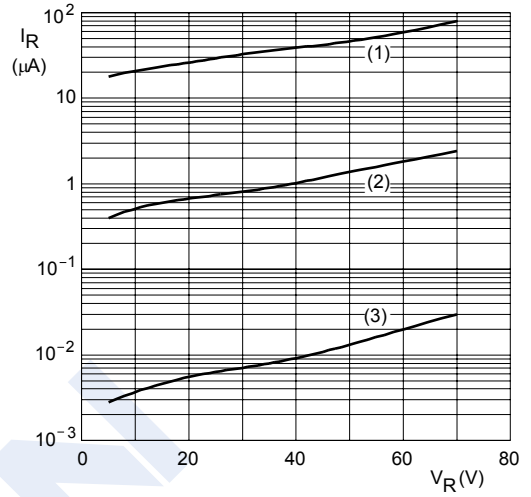
(1) T_{amb} = 125 °C. (3) T_{amb} = 25 °C.
(2) T_{amb} = 85 °C.

Fig.2 Reverse current as a function of reverse voltage; typical values.
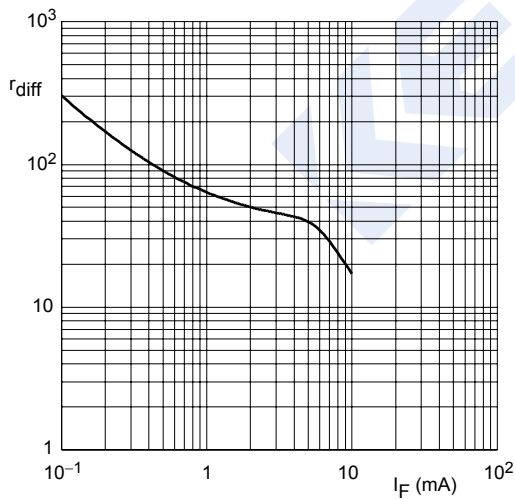
f = 10 kHz.

Fig.3 Differential forward resistance as a function of forward current; typical values.
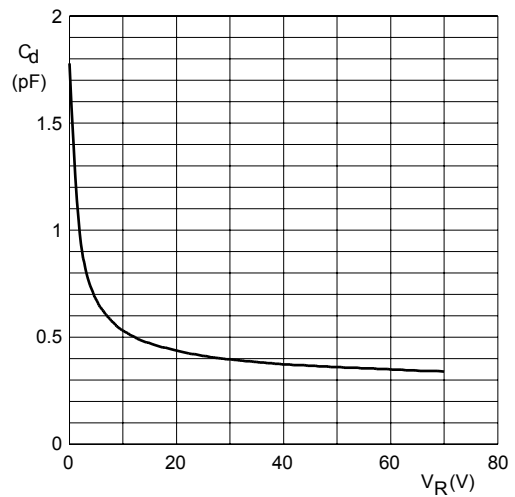
f = 1 MHz.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

KEXIN